



## 2SB1016

## PNP EPITAXIAL SILICON TRANSISTOR

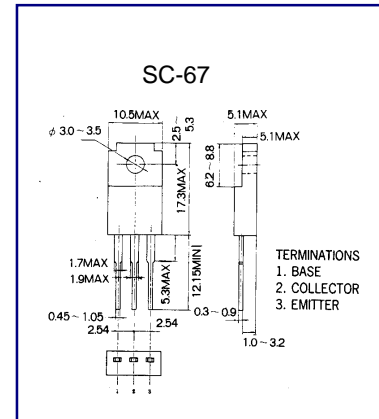
### POWER AMPLIFIER

### VERTICAL DEFLECTION OUTPUT

- Complement to 2SD1407

### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

| Characteristic                                   | Symbol    | Rating  | Unit             |
|--|-----------|---------|------------------|
| Collector-Base Voltage                           | $V_{CB0}$ | -100    | V                |
| Collector-Emitter Voltage                        | $V_{CE0}$ | -100    | V                |
| Emitter-Base voltage                             | $V_{EB0}$ | -5      | V                |
| Collector Current (DC)                           | $I_C$     | -3      | A                |
| Collector Dissipation ( $T_c=25^\circ\text{C}$ ) | $P_C$     | 25      | W                |
| Junction Temperature                             | $T_j$     | 150     | $^\circ\text{C}$ |
| Storage Temperature                              | $T_{stg}$ | -50~150 | $^\circ\text{C}$ |



### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ )

| Characteristic                        | Symbol        | Test Condition                              | Min | Typ | Max  | Unit          |
|---------------------------------------|---------------|---|-----|-----|------|---------------|
| Collector Cutoff Current              | $I_{CBO}$     | $V_{CB} = -150\text{V}, I_E = 0$            |     |     | -10  | $\mu\text{A}$ |
| Emitter Cutoff Current                | $I_{EBO}$     | $V_{EB} = -5\text{V}, I_C = 0$              |     |     | -10  | $\mu\text{A}$ |
| DC Current Gain                       | $h_{FE1}$     | $V_{CE} = -5.0\text{V}, I_C = -1.0\text{A}$ |     | 100 |      |               |
| Collector- Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = -4\text{A}, I_B = -0.4\text{mA}$     |     |     | -2.0 | V             |
| Current Gain Bandwidth Product        | $f_T$         | $V_{CE} = -10\text{V}, I_C = -0.5\text{A}$  |     | 60  |      | MHZ           |